



## A625308 Series

*Preliminary*

**32K X 8 BIT CMOS SRAM**

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### Document Title

**32K X 8 BIT CMOS SRAM**

### Revision History

<u>Rev. No.</u>	<u>History</u>	<u>Issue Date</u>	<u>Remark</u>
0.0	Initial issue	June 30, 1998	Preliminary
0.1	Erase 28-pin DIP package type	May 21, 1999	
0.2	Erase 55ns part	December 1, 2000	



# A625308 Series

## Preliminary

## 32K X 8 BIT CMOS SRAM

### Features

- External Operating Voltage: 4.5V to 5.5V
- Access times: 70 ns (max.)
- Current:
  - A625308-L series: Operating: 70mA (max.)  
Standby: 100µA (max.)
  - A625308-S series: Operating: 70mA (max.)  
Standby: 25µA (max.)
- Full static operation, no clock or refreshing required
- All inputs and outputs are directly TTL compatible
- Common I/O using three-state output
- Data retention voltage: 2.0V (min.)
- Available in 28-pin SOP and TSOP (forward and reverse type) packages

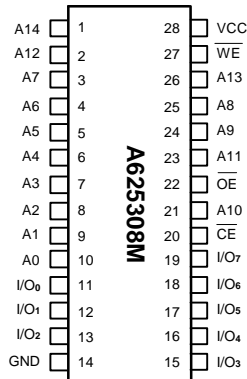
### General Description

The A625308 is a low operating current 262,144-bit static random access memory organized as 32,768 words by 8 bits and operates on a single 5V power supply. Inputs and three-state outputs are TTL compatible and allow for direct interfacing with common system bus structures.

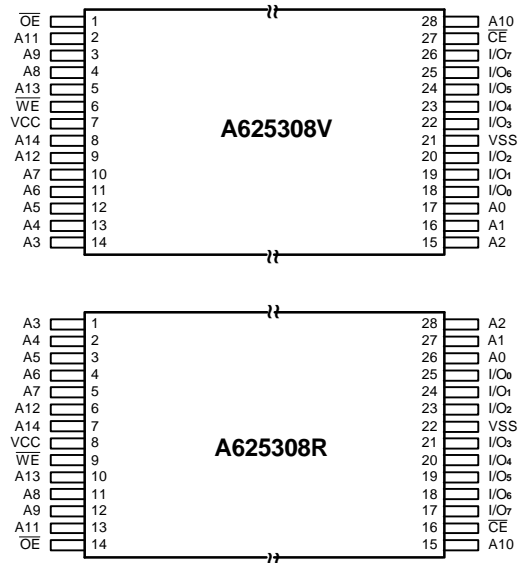
Minimum standby power is drawn by this device when  $\overline{CE}$  is at a high level, independent of the other input levels. Data retention is guaranteed at a power supply voltage as low as 2.0V.

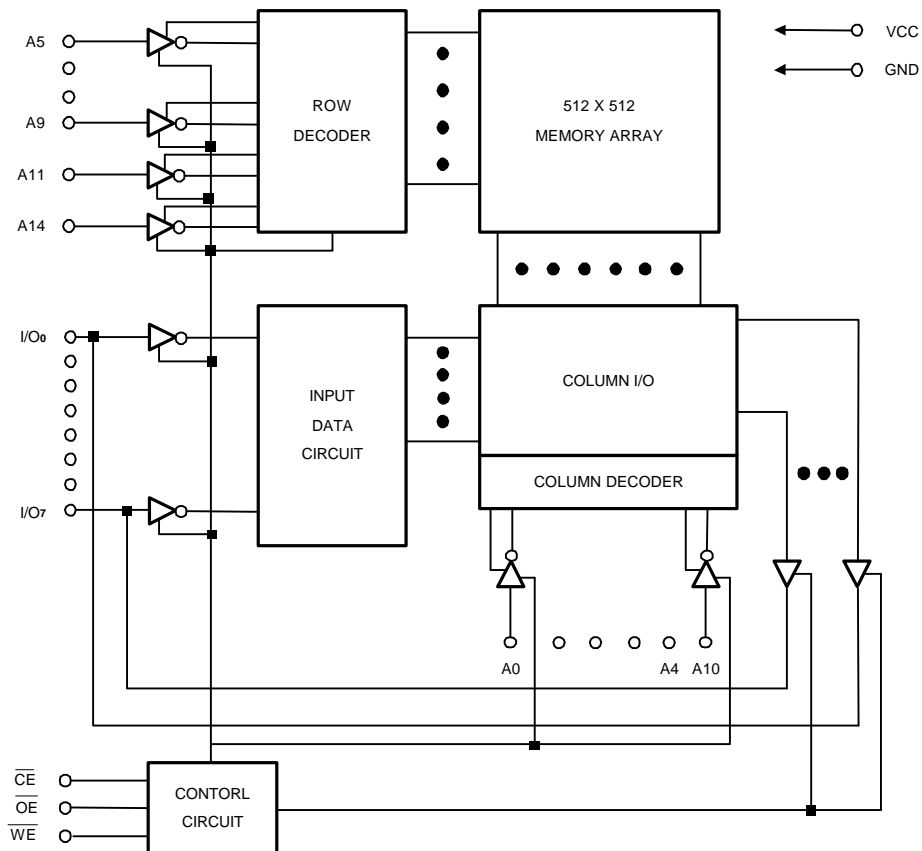
### Pin Configurations

#### ■ SOP



#### ■ TSOP



**Block Diagram**

**Pin Descriptions - SOP**

Pin No.	Symbol	Description
1-10, 21, 23-26	A0 - A14	Address Input
11-13, 15-19	I/O <sub>0</sub> - I/O <sub>7</sub>	Data Inputs/Outputs
14	GND	Ground
20	$\overline{CE}$	Chip Enable
22	$\overline{OE}$	Output Enable
27	$\overline{WE}$	Write Enable
28	VCC	Power Supply

**Pin Description-TSOP**

Pin No.	Symbol	Description
1	$\overline{OE}$	Output Enable
2-5, 8-17, 28	A0 - A14	Address Input
7	VCC	Power Supply
6	$\overline{WE}$	Write Enable
18-20, 22-26	I/O <sub>0</sub> - I/O <sub>7</sub>	Data Inputs/Outputs
21	GND	Ground
27	$\overline{CE}$	Chip Enable

**Recommended DC Operating Conditions**

 (T<sub>A</sub> = 0°C to +70°C)

Symbol	Parameter	Min.	Typ.	Max.	Unit
VCC	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
V <sub>IH</sub>	Input High Voltage	2.2	3.5	VCC + 0.3	V
V <sub>IL</sub>	Input Low Voltage	-0.3	0	+0.8	V

**Absolute Maximum Ratings\***

VCC to GND . . . . . -0.5V to +7.0V  
 IN, IN/OUT Volt to GND . . . . . -0.5V to VCC + 0.5V  
 Operating Temperature, Topr . . . . . 0°C to +70°C  
 Storage Temperature, Tstg . . . . . -55°C to +125°C  
 Power Dissipation, P<sub>T</sub> . . . . . 0.7W  
 Soldering Temp. & Time . . . . . 260°C, 10 sec

**\*Comments**

Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only. Functional operation of this device at these or any other conditions above those indicated in the operational sections of this specification is not implied and exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**DC Electrical Characteristics (T<sub>A</sub> = 0°C to +70°C, VCC = 5.0V ± 10%, GND = 0V)**

Symbol	Parameter	A625308-70L		A625308-70S		Unit	Conditions
		Min.	Max.	Min.	Max.		
I <sub>LI</sub>	Input Leakage Current	-	1	-	1	μA	V <sub>IN</sub> = GND to VCC
I <sub>LO</sub>	Output Leakage Current	-	1	-	1	μA	$\overline{CE} = V_{IH}$ or $\overline{OE} = V_{IH}$ or V <sub>WE</sub> = V <sub>IH</sub> V <sub>I/O</sub> = GND to VCC
I <sub>CC</sub>	Active Power Supply Current	-	15	-	15	mA	$\overline{CE} = V_{IL}$ , I <sub>I/O</sub> = 0mA
I <sub>CC1</sub>	Dynamic Operating Current	-	70	-	70	mA	Min. Cycle, Duty = 100% $\overline{CE} = V_{IL}$ , I <sub>I/O</sub> = 0mA
I <sub>CC2</sub>	Dynamic Operating Current	-	15	-	15	mA	$\overline{CE} = V_{IL}$ , V <sub>IH</sub> = VCC V <sub>IL</sub> = 0V, f = 1 MHz I <sub>I/O</sub> = 0 mA

**DC Electrical Characteristics (continued)**

Symbol	Parameter	A625308-70L		A625308-70S		Unit	Conditions
		Min.	Max.	Min.	Max.		
I <sub>SB</sub>	Supply Current Standby Power	-	3	-	2	mA	$\overline{CE} = V_{IH}$
I <sub>SB1</sub>		-	100	-	25	μA	$\overline{CE} \geq V_{CC} - 0.2V$ $V_{IN} \geq 0V$
V <sub>oL</sub>	Output Low Voltage	-	0.4	-	0.4	V	I <sub>oL</sub> = 2.1mA
V <sub>oH</sub>	Output High Voltage	2.4	-	2.4	-	V	I <sub>oH</sub> = -1.0mA

**Truth Table**

Mode	$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	I/O Operation	Supply Current
Standby	H	X	X	High Z	I <sub>SB</sub> , I <sub>SB1</sub>
Output Disable	L	H	H	High Z	I <sub>CC</sub> , I <sub>CC1</sub> , I <sub>CC2</sub>
Read	L	L	H	Dout	I <sub>CC</sub> , I <sub>CC1</sub> , I <sub>CC2</sub>
Write	L	X	L	Din	I <sub>CC</sub> , I <sub>CC1</sub> , I <sub>CC2</sub>

Note: X: H or L

**Capacitance** (T<sub>A</sub> = 25°C, f = 1.0 MHz)

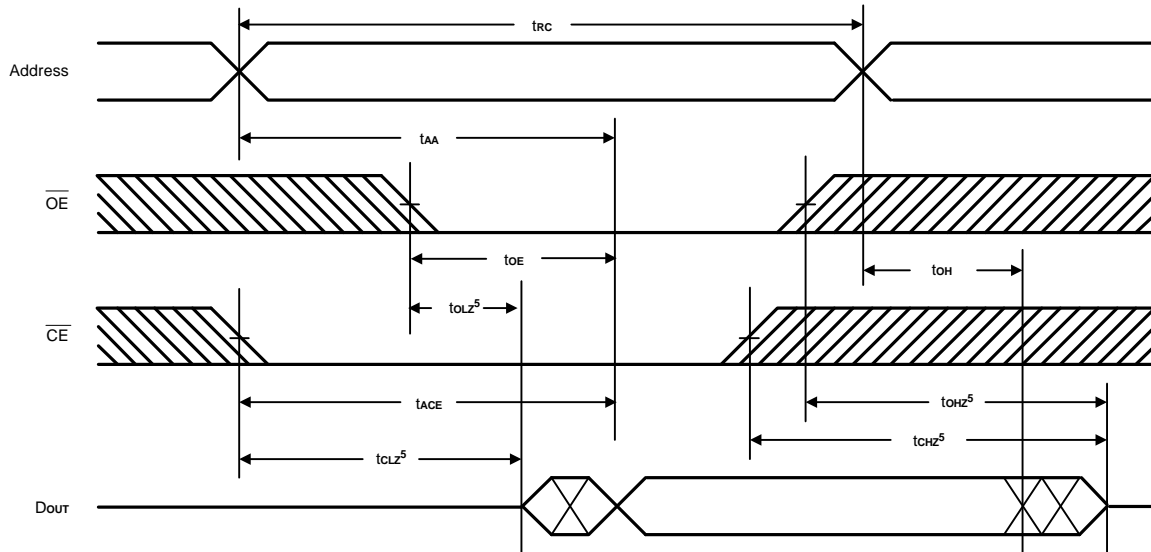
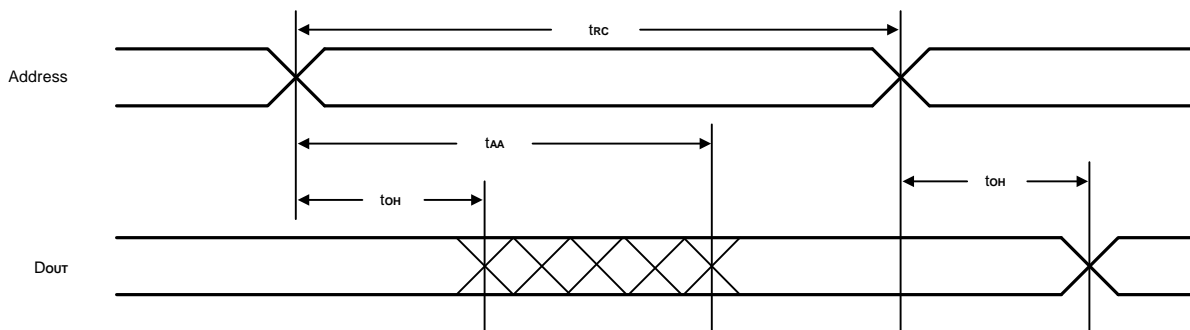
Symbol	Parameter	Min.	Max.	Unit	Conditions
C <sub>IN</sub> *	Input Capacitance		6	pF	V <sub>IN</sub> = 0V
C <sub>I/O</sub> *	Input/Output Capacitance		8	pF	V <sub>I/O</sub> = 0V

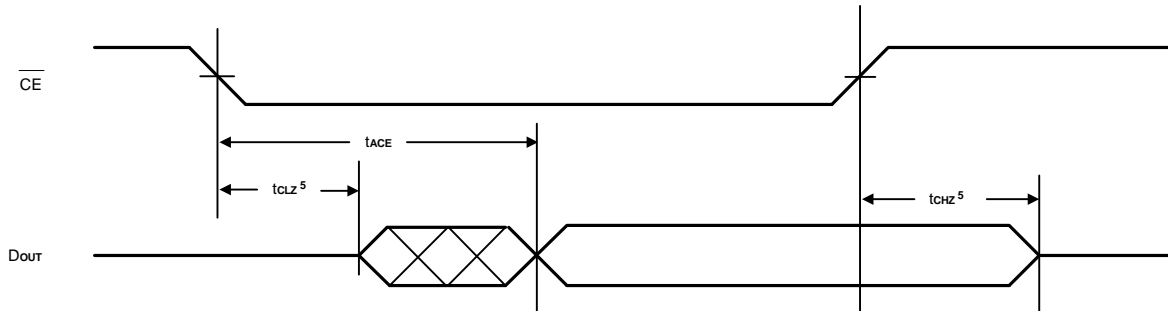
\* These parameters are sampled and not 100% tested.

**AC Characteristics** ( $T_A = 0^\circ\text{C}$  to  $+70^\circ\text{C}$ ,  $V_{CC} = 5.0\text{V} \pm 10\%$ )

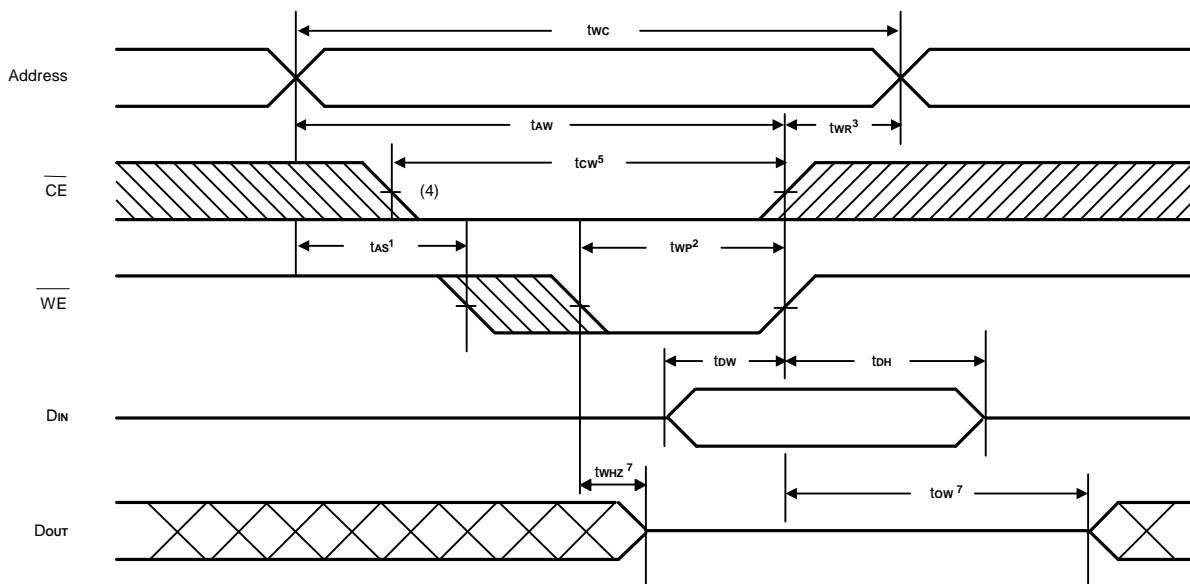
Symbol	Parameter	A625308-70L/70S		Unit
		Min.	Max.	
Read Cycle				
t <sub>RC</sub>	Read Cycle Time	70	-	ns
t <sub>AA</sub>	Address Access Time	-	70	ns
t <sub>ACE</sub>	Chip Enable Access Time	-	70	ns
t <sub>OE</sub>	Output Enable to Output Valid	-	35	ns
t <sub>CLZ</sub>	Chip Enable to Output in Low Z	10	-	ns
t <sub>OLZ</sub>	Output Enable to Output in Low Z	5	-	ns
t <sub>CHZ</sub>	Chip Disable to Output in High Z	-	25	ns
t <sub>OHZ</sub>	Output Disable to Output in High Z	-	25	ns
t <sub>OH</sub>	Output Hold from Address Change	5	-	ns
Write Cycle				
t <sub>WC</sub>	Write Cycle Time	70	-	ns
t <sub>CW</sub>	Chip Enable to End of Write	60	-	ns
t <sub>AS</sub>	Address Set up Time	0	-	ns
t <sub>AW</sub>	Address Valid to End of Write	60	-	ns
t <sub>WP</sub>	Write Pulse Width	50	-	ns
t <sub>WR</sub>	Write Recovery Time	0	-	ns
t <sub>WHZ</sub>	Write to Output in High Z	-	30	ns
t <sub>DW</sub>	Data to Write Time Overlap	30	-	ns
t <sub>DH</sub>	Data Hold from Write Time	0	-	ns
t <sub>OW</sub>	Output Active from End of Write	5	-	ns

Notes: t<sub>CHZ</sub>, t<sub>OHZ</sub> and t<sub>WHZ</sub> are defined as the time at which the outputs achieve the open circuit condition and are not referred to output voltage levels.

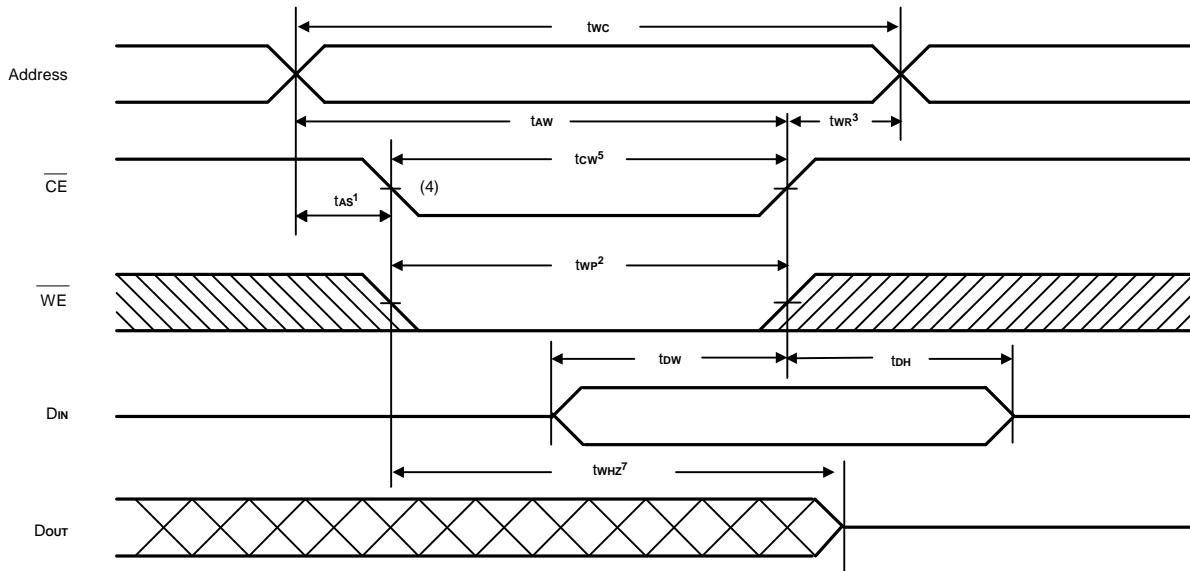
**Timing Waveforms**
**Read Cycle 1 <sup>(1)</sup>**

**Read Cycle 2 <sup>(1, 2, 4)</sup>**


**Timing Waveforms (continued)**
**Read Cycle 3<sup>(1, 3, 4)</sup>**


- Notes:
1.  $\overline{WE}$  is high for Read Cycle.
  2. Device is continuously enabled,  $\overline{CE} = V_{IL}$ .
  3. Address valid prior to or coincident with  $\overline{CE}$  transition low.
  4.  $\overline{OE} = V_{IL}$ .
  5. Transition is measured  $\pm 500\text{mV}$  from steady state. This parameter is sampled and not 100% tested.

**Write Cycle 1<sup>(6)</sup>  
(Write Enable Controlled)**


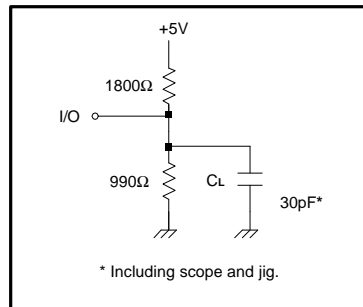
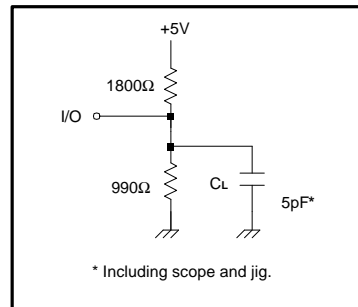


**Timing Waveforms (continued)**
**Write Cycle 2 <sup>(6)</sup>  
(Chip Enable Controlled)**


- Notes:
1.  $t_{AS}$  is measured from the address valid to the beginning of Write.
  2. A Write occurs during the overlap ( $t_{WP}$ ) of a low  $\overline{CE}$  and a low  $\overline{WE}$ .
  3.  $t_{WR}$  is measured from the earliest of  $\overline{CE}$  or  $\overline{WE}$  going high to the end of the Write cycle.
  4. If the  $\overline{CE}$  low transition occurs simultaneously with the  $\overline{WE}$  low transition or after the  $\overline{WE}$  transition, outputs remain in a high impedance state.
  5.  $t_{CW}$  is measured from the later of  $\overline{CE}$  going low to the end of Write.
  6.  $\overline{OE}$  level is high or low.
  7. Transition is measured  $\pm 500\text{mV}$  from steady. This parameter is sampled and not 100% tested.

**AC Test Conditions**

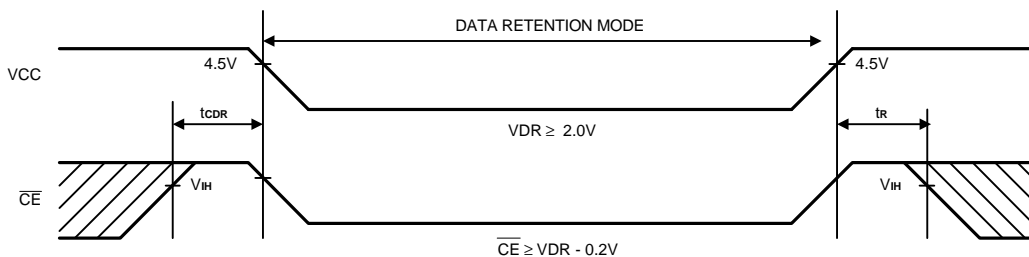
Input Pulse Levels	0V, 3.0V
Input Rise And Fall Time	5 ns
Input and Output Timing Reference Levels	1.5V
Output Load	See Figure 1,2


**Figure 1. Output Load**

**Figure 2. Output Load for t<sub>CLZ</sub>  
t<sub>OLZ</sub>, t<sub>CHZ</sub>, t<sub>OHZ</sub>, t<sub>WHZ</sub>, and t<sub>OW</sub>**
**Data Retention Characteristics (T<sub>A</sub> = 0°C to 70°C)**

Symbol	Parameter	Min.	Max.	Unit	Conditions
V <sub>DR</sub>	VCC for Data Retention	2.0	5.5	V	$\overline{CE} \geq VCC - 0.2V$
I <sub>CCDR</sub>	Data Retention Current	L Version	50*	μA	VCC = 3.0V, $\overline{CE} \geq VCC - 0.2V$ V <sub>IN</sub> ≥ 0V
		S Version	10**		
t <sub>CDR</sub>	Chip Disable to Data Retention Time	0	-	ns	See Retention Waveform
t <sub>R</sub>	Operation Recovery Time	5	-	ms	

\* A625308-70L      I<sub>CCDR</sub> : Max. 20μA at T<sub>A</sub> = 0°C to +40°C

\*\* A625308-70S      I<sub>CCDR</sub> : Max. 3μA at T<sub>A</sub> = 0°C to +40°C

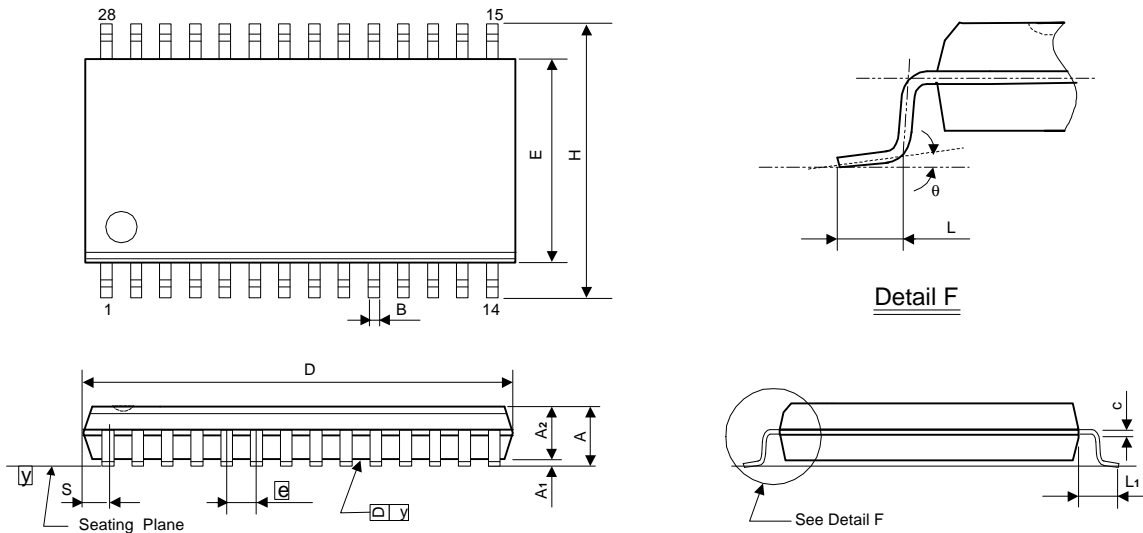
**Low VCC Data Retention Waveform**


**Ordering Information**

Part No.	Access Time (ns)	Operating Current Max. (mA)	Standby Current Max. ( $\mu$ A)	Package
A625308M-70L	70	70	100	28L SOP
A625308M-70S		70	25	28L SOP
A625308V-70L		70	100	28L TSOP (Forward)
A625308V-70S		70	25	28L TSOP (Forward)
A625308R-70L		70	100	28L TSOP (Reverse)
A625308R-70S		70	25	28L TSOP (Reverse)

**Package Information**
**SOP (W.B.) 28L Outline Dimensions**

unit: inches/mm



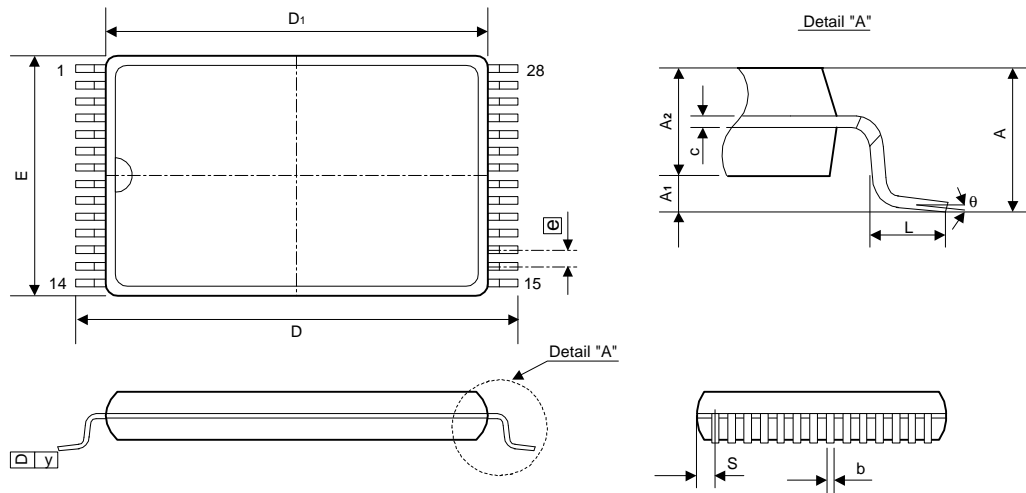
Symbol	Dimensions in inches			Dimensions in mm		
	Min	Nom	Max	Min	Nom	Max
A	-	-	0.112	-	-	2.85
A1	0.004	-	-	0.10	-	-
A2	0.093	0.098	0.103	2.36	2.49	2.62
B	0.014	0.016	0.020	0.36	0.41	0.51
C	0.008	0.010	0.012	0.20	0.25	0.30
D	-	0.713	0.728	-	18.11	18.49
E	0.326	0.331	0.336	8.28	8.41	8.53
$\bar{e}$	0.044	0.050	0.056	1.12	1.27	1.42
H	0.453	0.465	0.477	11.51	11.81	12.12
L	0.028	0.036	0.044	0.71	0.91	1.12
L1	0.059	0.067	0.075	1.50	1.70	1.91
S	-	-	0.047	-	-	1.19
y	-	-	0.004	-	-	0.10
$\theta$	0°	-	8°	0°	-	8°

**Notes:**

1. The maximum value of dimension D includes end flash.
2. Dimension E does not include resin fins.
3. Dimension S includes end flash.

**Package Information**
**TSOP 28L TYPE I (8 X 13.4mm) Outline Dimensions**

unit: inches/mm



Symbol	Dimensions in inches			Dimensions in mm		
	Min	Nom	Max	Min	Nom	Max
A	-	-	0.049	-	-	1.25
A <sub>1</sub>	0.002	-	-	0.05	-	-
A <sub>2</sub>	0.037	0.039	0.041	0.95	1.00	1.05
b	0.007	0.009	0.011	0.17	0.22	0.27
c	0.005	-	0.008	0.12	-	0.21
E	0.311	0.315	0.319	7.90	8.00	8.10
L	0.012	0.020	0.028	0.30	0.50	0.70
D	0.520	0.528	0.536	13.20	13.40	13.60
D <sub>1</sub>	0.461	0.465	0.469	11.70	11.80	11.90
e	0.022 BSC			0.55 BSC		
S	0.017 TYP			0.425 TYP		
y	-	-	0.004	-	-	0.10
θ	0°	-	5°	0°	-	5°

**Notes:**

1. The maximum value of dimension D<sub>1</sub> includes end flash.
2. Dimension E does not include resin fins.
3. Dimension S includes end flash.